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Photodiode Chip IR

EOPC-880-0.9-1

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Radiation	Type	Electrodes
infrared, selective	AlGaAs/GaAs, integrated filter	P (anode) up

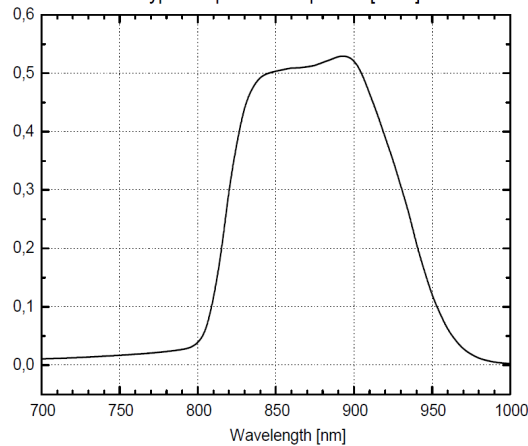
	Description:
	infrared-selective photodiode with narrow response range: 810...950 nm @ 10% of max. responsivity
	Applications:
	Optical communications, safety equipment, light barriers
	Typical dimensions:
	typ. thickness: 300 µm anode: gold alloy, thickness: 2.1 µm cathode: gold alloy, thickness: 0.5 µm active area: 0.72 mm ²

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameters	Test conditions	Min	Typ	Max	Unit
Dark current	V _R = 1 V		1	2.5	nA
Reverse voltage	I _R = 10 µA	5			V
WL of peak sensitivity	V _R = 0 V		890		nm
Spectral range @ 50% lower limit	V _R = 0 V	820		935	nm
FWHM	V _R = 0 V		115		nm
Responsivity, bare chip @ λ _p	V _R = 0 V	0.15	0.25		A/W
Responsivity, epoxy covered chip @ λ _p	V _R = 0 V		0.55		A/W

Typical spectral response [A/W]



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We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.